



New Product

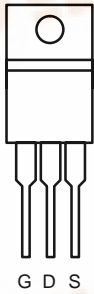
SUP/SUB65P04-15

Vishay Siliconix

P-Channel 40-V (D-S) 175°C MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
-40	0.015 @ V _{GS} = -10 V	-65
	0.023 @ V _{GS} = -4.5 V	-50

TO-220AB

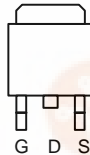


Top View

SUP65P04-15

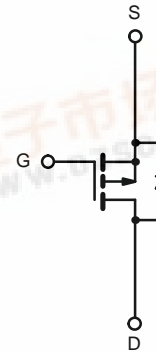
DRAIN connected to TAB

TO-263



Top View

SUB65P04-15



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25°C UNLESS OTHERWISE NOTED)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-40	V
Gate-Source Voltage	V _{GS}	±20	
Continuous Drain Current (T _J = 175°C)	I _D	T _C = 25°C	-65
		T _C = 125°C	-37
Pulsed Drain Current	I _{DM}	-240	A
Avalanche Current	I _{AR}	-60	
Repetitive Avalanche Energy ^a	E _{AR}	180	mJ
Power Dissipation	P _D	T _C = 25°C (TO-220AB and TO-263)	120°
		T _A = 25°C (TO-263) ^b	3.75
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient	PCB Mount (TO-263) ^b	40	°C/W
	Free Air (TO-220AB)	62.5	
Junction-to-Case	R _{thJC}	1.25	

Notes:
 a. Duty cycle ≤ 1%.
 b. When mounted on 1" square PCB (FR-4 material).
 c. See SOA curve for voltage derating.



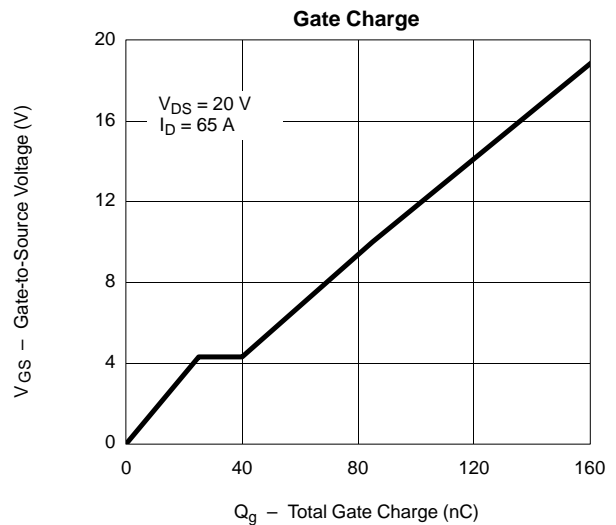
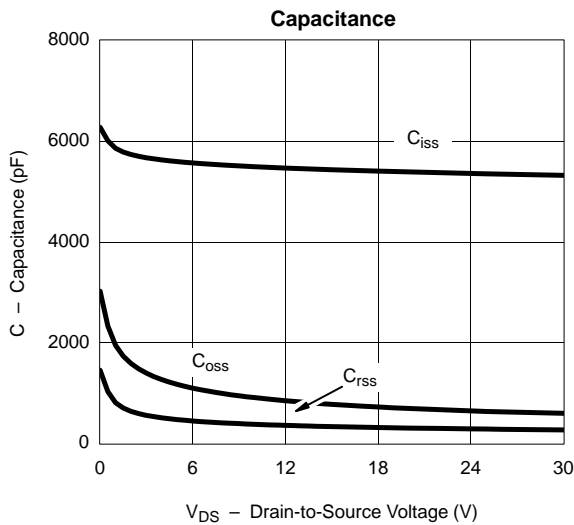
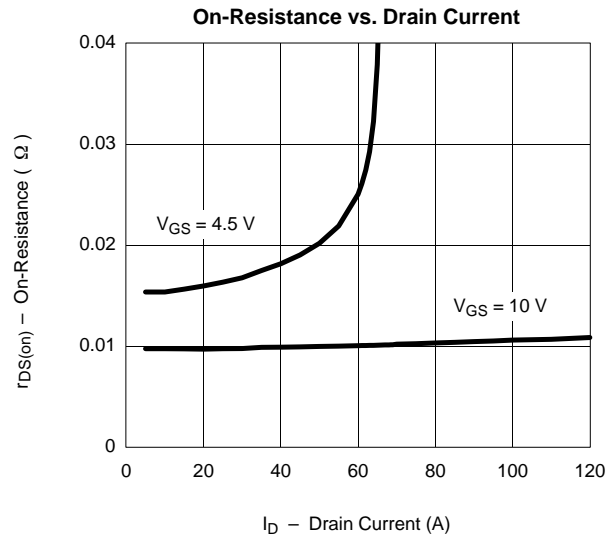
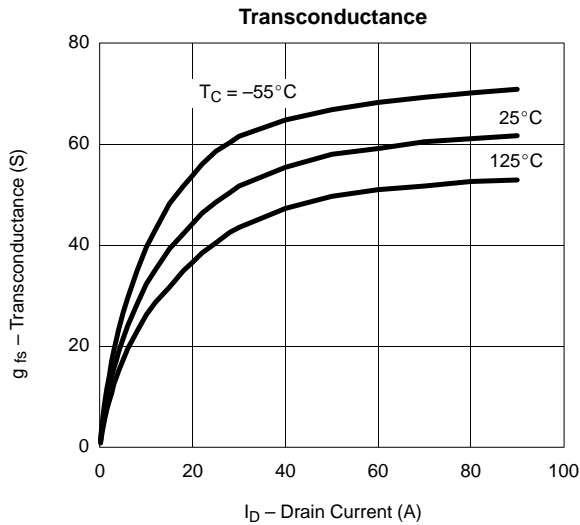
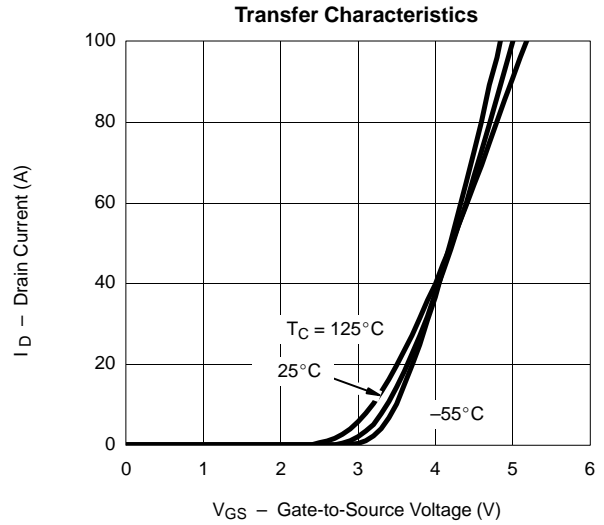
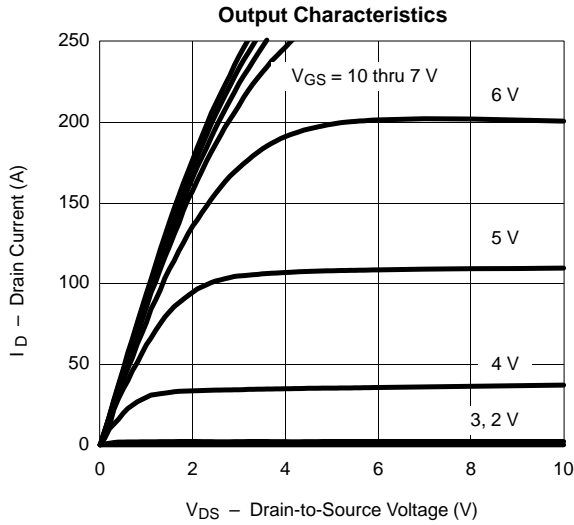
SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = -250 μA	-40			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-1		-3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -40 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -40 V, V _{GS} = 0 V, T _J = 125 °C			-50	
		V _{DS} = -40 V, V _{GS} = 0 V, T _J = 175 °C			-250	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = -5 V, V _{GS} = -10 V	-120			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = -10 V, I _D = -30 A		0.012	0.015	Ω
		V _{GS} = -10 V, I _D = -30 A, T _J = 125 °C			0.024	
		V _{GS} = -10 V, I _D = -30 A, T _J = 175 °C			0.030	Ω
		V _{GS} = -4.5 V, I _D = -20 A		0.018	0.023	
Forward Transconductance ^a	g _{fs}	V _{DS} = -15 V, I _D = -50 A	20			S
Dynamic^b						
Input Capacitance	C _{iSS}	V _{GS} = 0 V, V _{DS} = -25 V, f = 1 MHz		5400		pF
Output Capacitance	C _{oss}			640		
Reverse Transfer Capacitance	C _{rSS}			300		
Total Gate Charge ^c	Q _g	V _{DS} = -20 V, V _{GS} = -10 V, I _D = -65 A		85	130	nC
Gate-Source Charge ^c	Q _{gs}			25		
Gate-Drain Charge ^c	Q _{gd}			15		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = -20 V, R _L = 0.3 Ω I _D = -65 A, V _{GEN} = -10 V, R _G = 2.5 Ω		15	25	ns
Rise Time ^c	t _r			380	580	
Turn-Off Delay Time ^c	t _{d(off)}			75	115	
Fall Time ^c	t _f			140	210	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)^b						
Continuous Current	I _s				-65	A
Pulsed Current	I _{SM}				-240	
Forward Voltage ^a	V _{SD}	I _F = -65 A, V _{GS} = 0 V		-1.2	-1.5	V
Reverse Recovery Time	t _{rr}	I _F = -65 A, di/dt = 100 A/μs		40	80	ns
Peak Reverse Recovery Current	I _{RM(REC)}			2.0	4	A
Reverse Recovery Charge	Q _{rr}			0.04	0.1	μC

Notes:

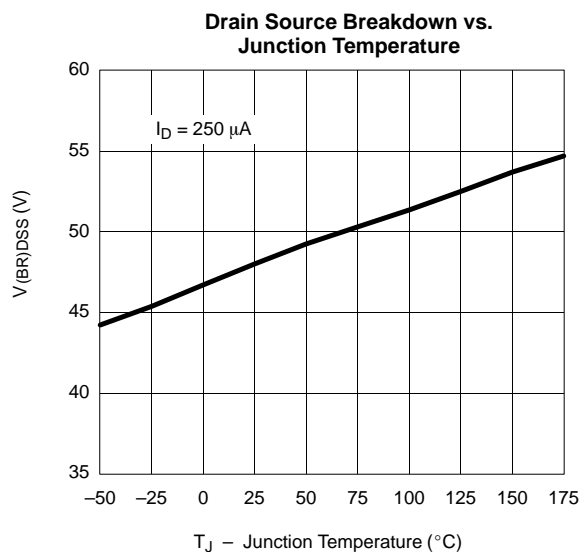
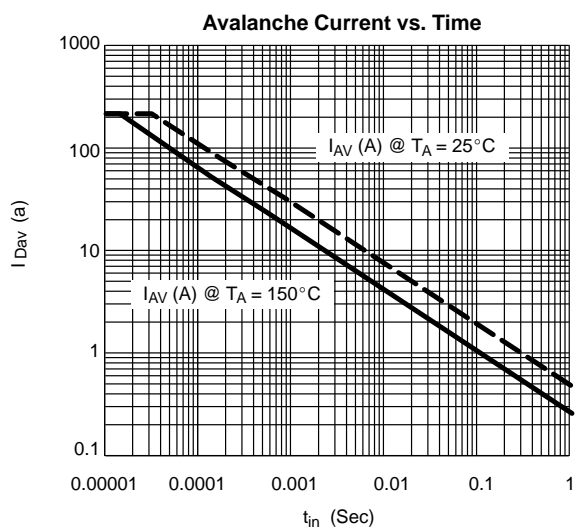
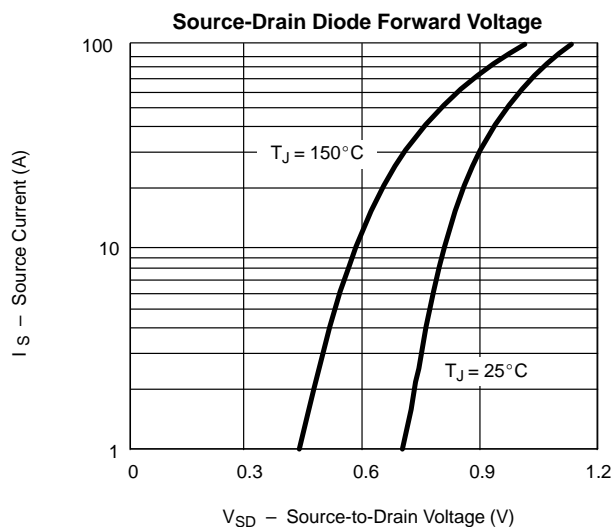
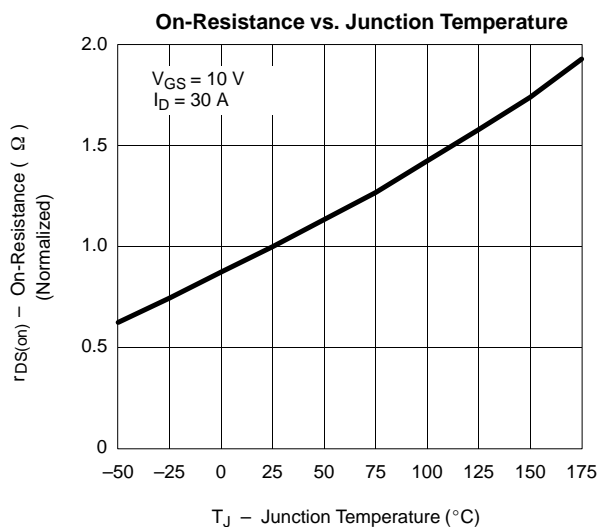
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



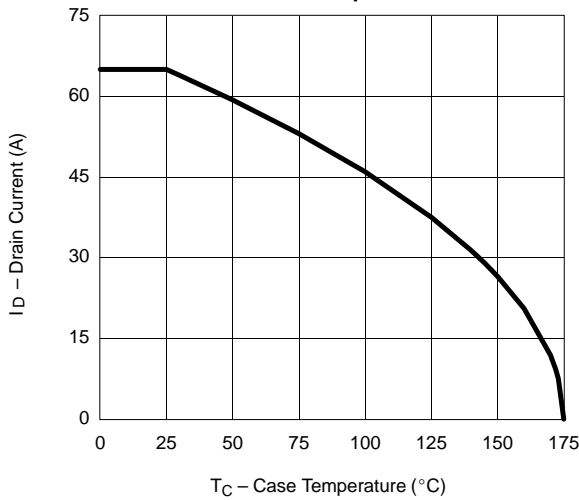
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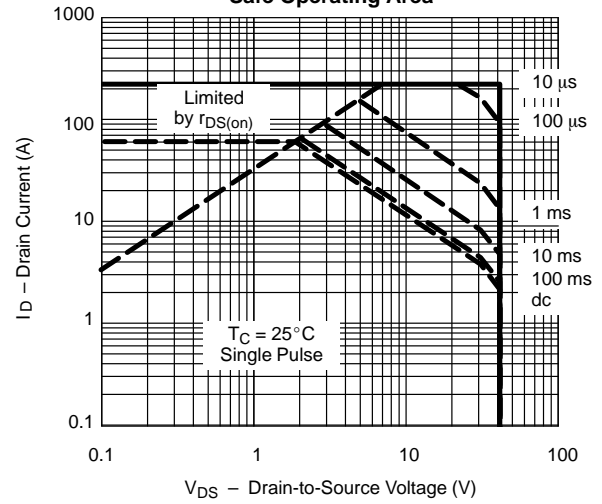


THERMAL RATINGS

Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

